

N-Channel Junction Silicon FET

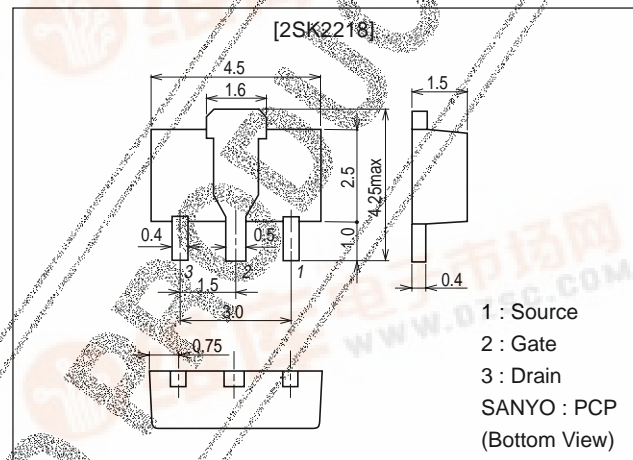
SANYO**2SK2218****High-Frequency Low-Noise Amplifier Applications****Features**

- Adoption of FBET process.
- Amateur radio equipment.
- UHF amplifiers, MIX, OSC, analog switches.
- Large $|y_{fs}|$.
- Small Ciss.

Package Dimensions

unit:mm

2125

**Specifications****Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$**

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		15	V
Gate-to-Drain Voltage	V_{GD}		-15	V
Gate Current	I_G		10	mA
Drain Current	I_D		100	mA
Allowable Power Dissipation	P_D	Mounted on ceramic board (250mm \times 0.8mm)	400	mW
Junction Temperature	T_J		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gate-to-Drain Breakdown Voltage	$V_{(BR)GDS}$	$I_G = -10\mu\text{A}$, $V_{DS} = 0$	-15			V
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = -10\text{V}$, $V_{DS} = 0$			-1.0	nA
Zero-Gate Voltage Drain Current	I_{DSS}^{**}	$V_{DS} = 5\text{V}$, $V_{GS} = 0$	40*		75*	mA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 5\text{V}$, $I_D = 100\mu\text{A}$	-1.2	-2.6	-4.5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = 5\text{V}$, $V_{GS} = 0$, $f = 1\text{kHz}$	24	32		mS

*: Pulse Test Pulse Width 2mS

*: The 2SK2218 is classified by I_{DSS} as follows (unit : mA).

40	3	52	48	4	63	57	5	75
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Marking: KN

 I_{DSS} ranks: 3, 4, 5

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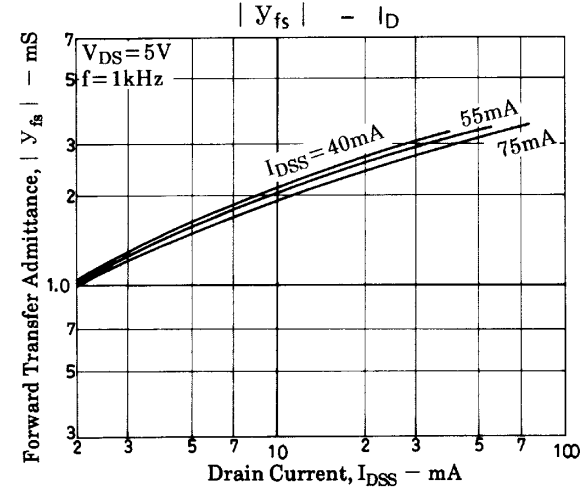
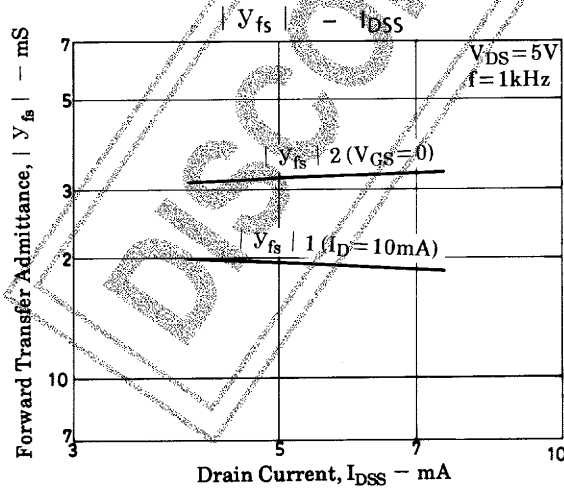
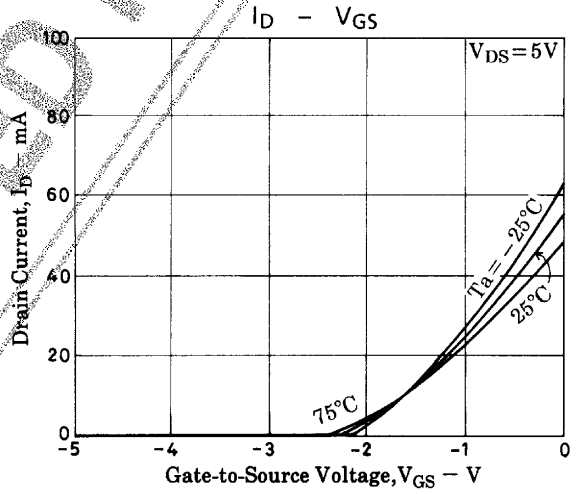
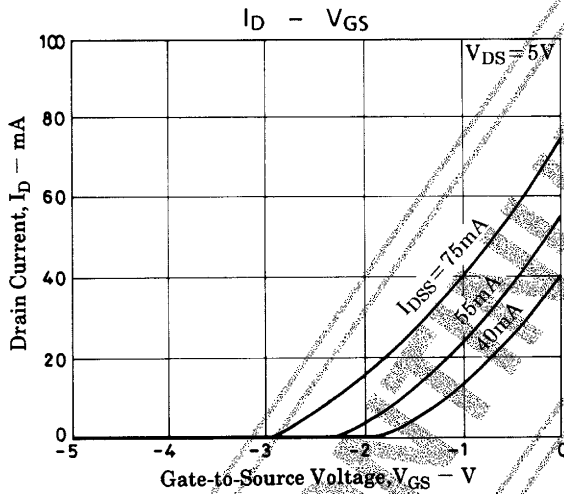
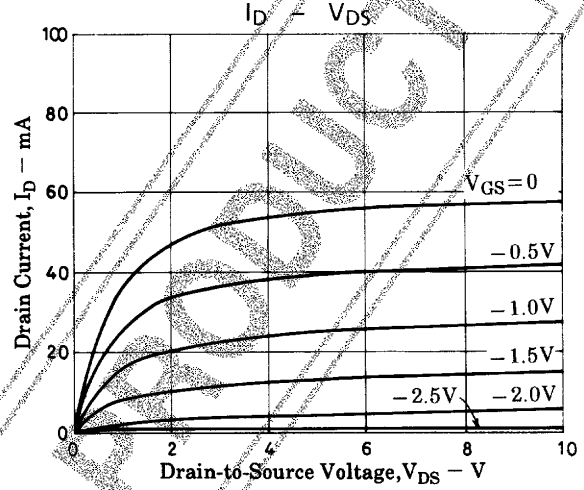
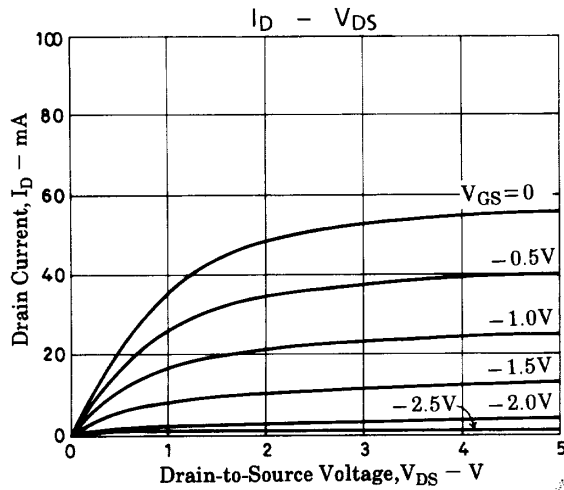
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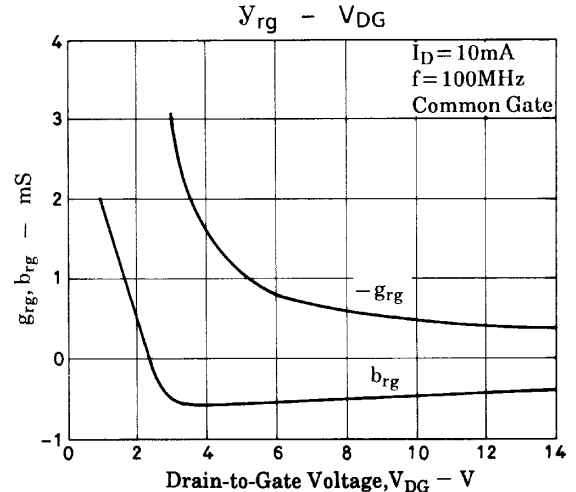
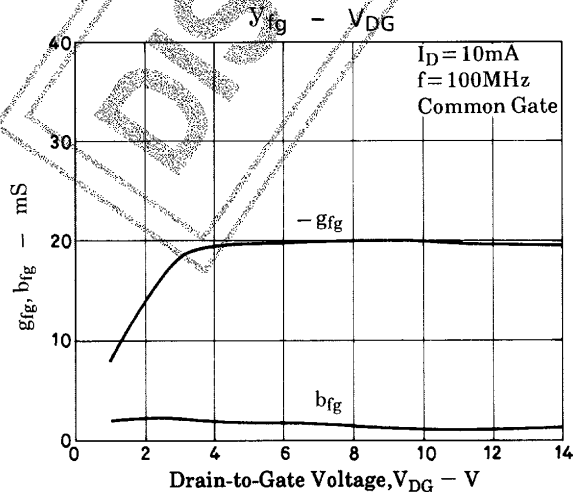
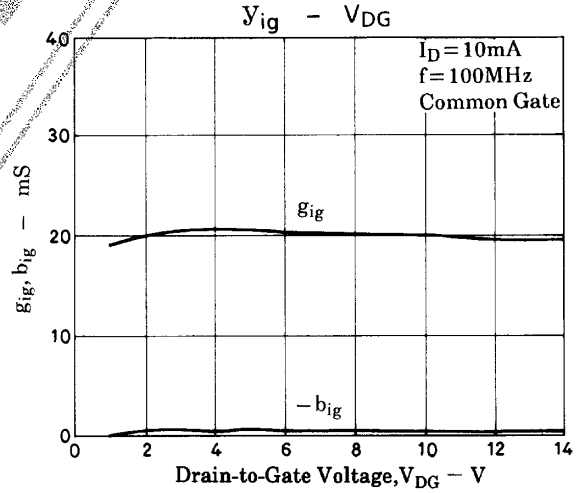
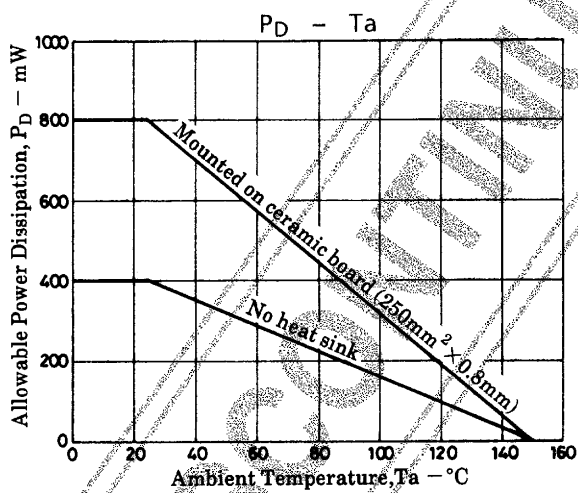
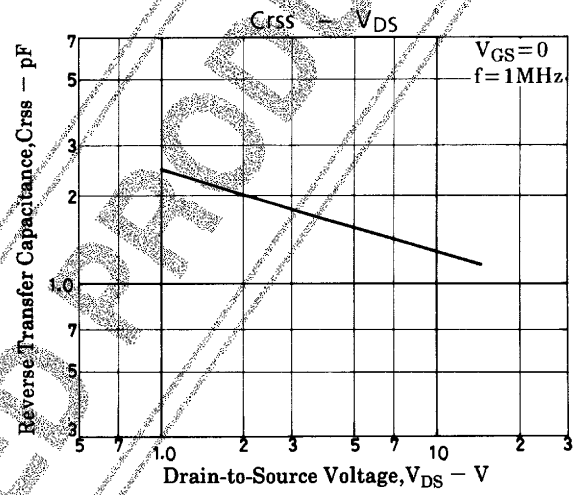
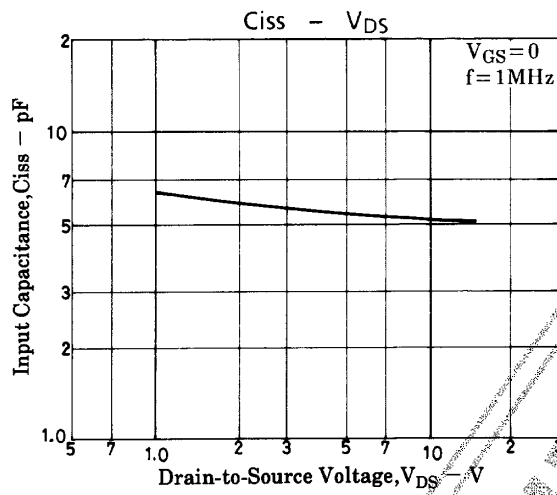
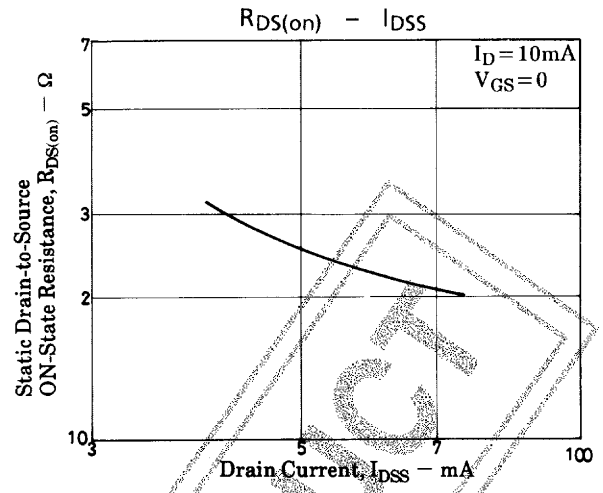
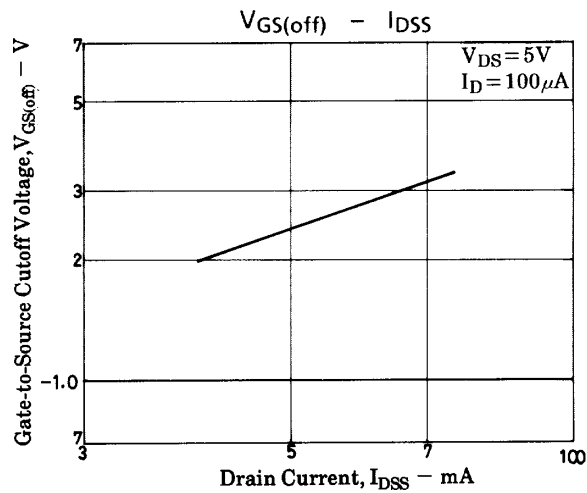
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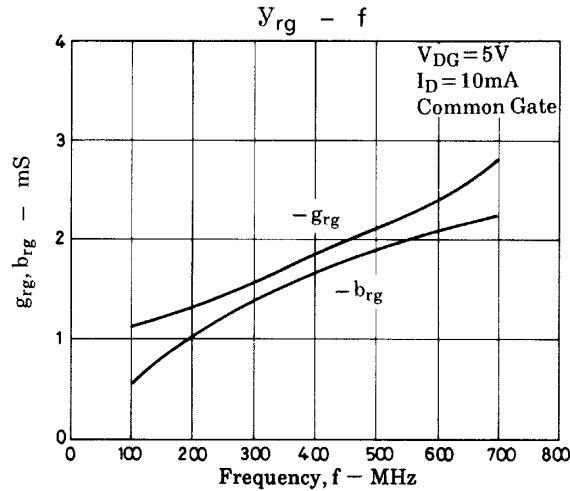
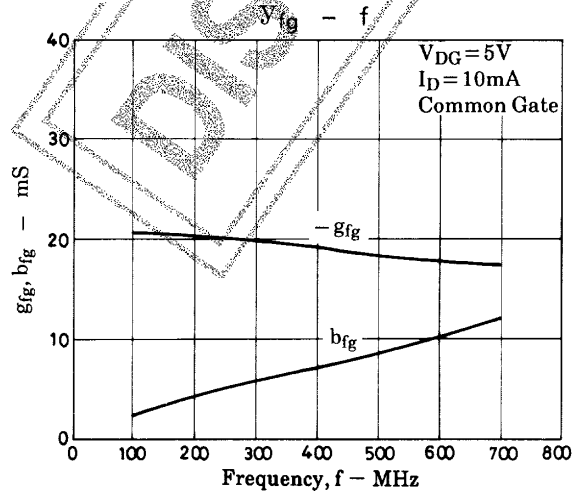
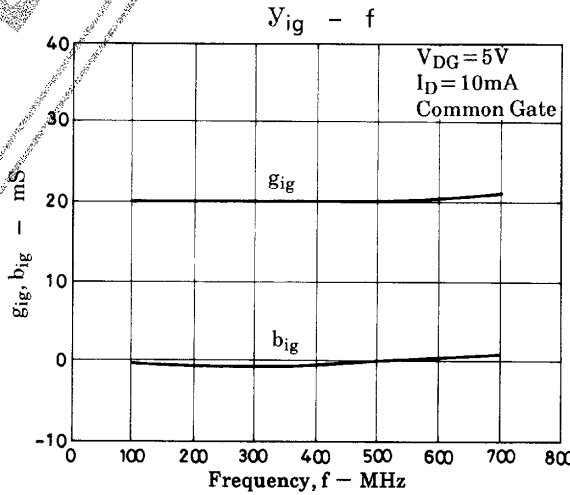
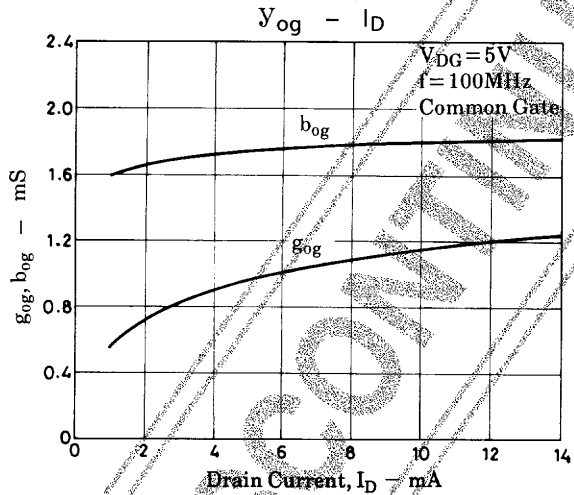
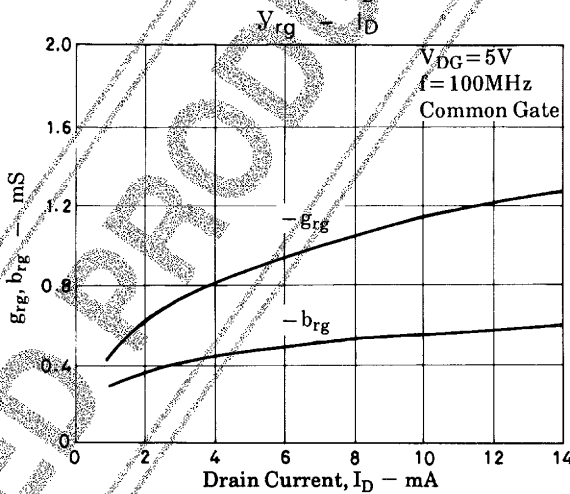
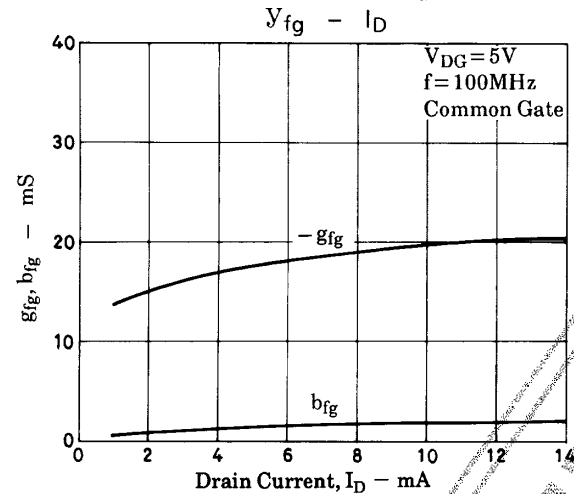
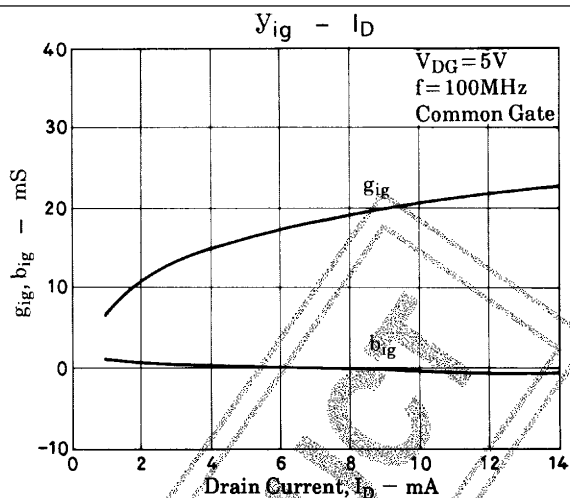
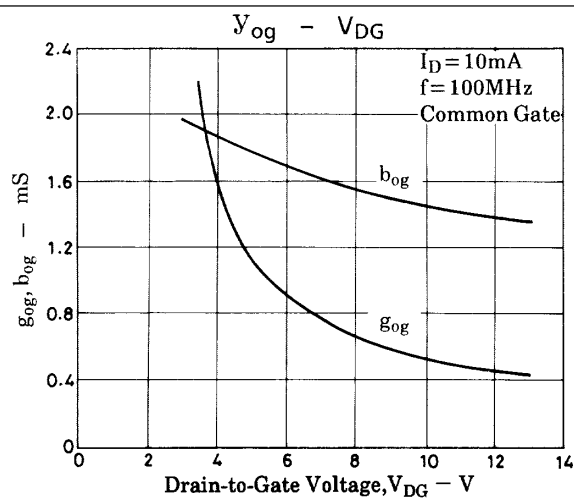
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	C_{iss}	$V_{DS}=5V, V_{GS}=0, f=1MHz$		5.5		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=5V, V_{GS}=0, f=1MHz$		1.6		pF
Noise Figure	NF	$V_{DS}=5V, R_g=1k\Omega, I_D=5mA, f=1kHz$		1.3		dB
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	$I_D=10mA, V_{GS}=0$		30		Ω



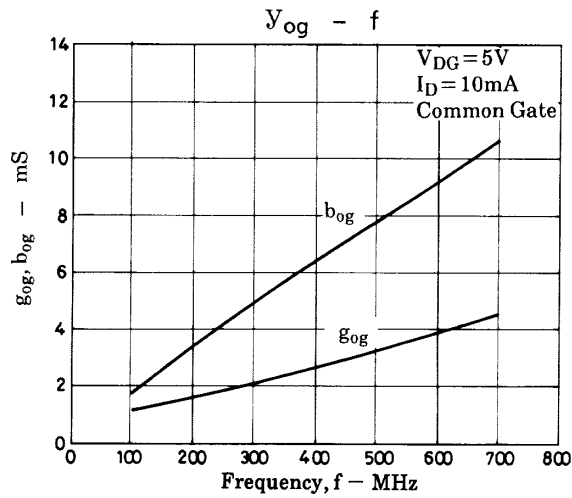
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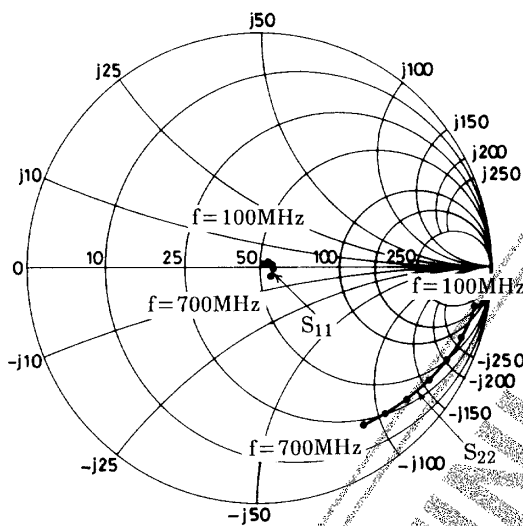


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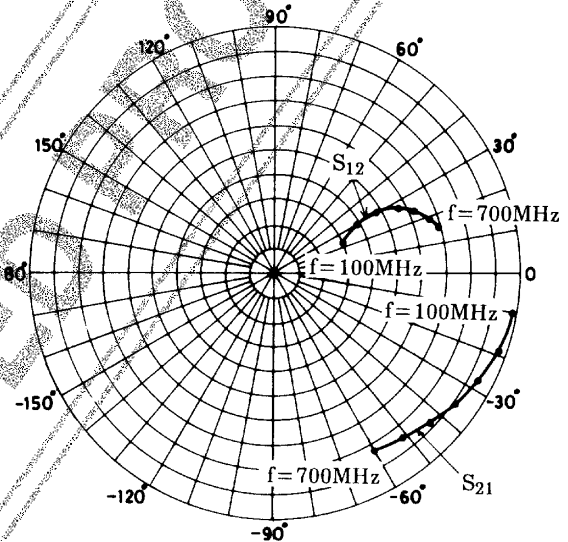
S parameter Frequency Characteristics

(Common gate) ($V_{DG}=5V$, $I_D=10mA$)



S parameter Frequency Characteristics

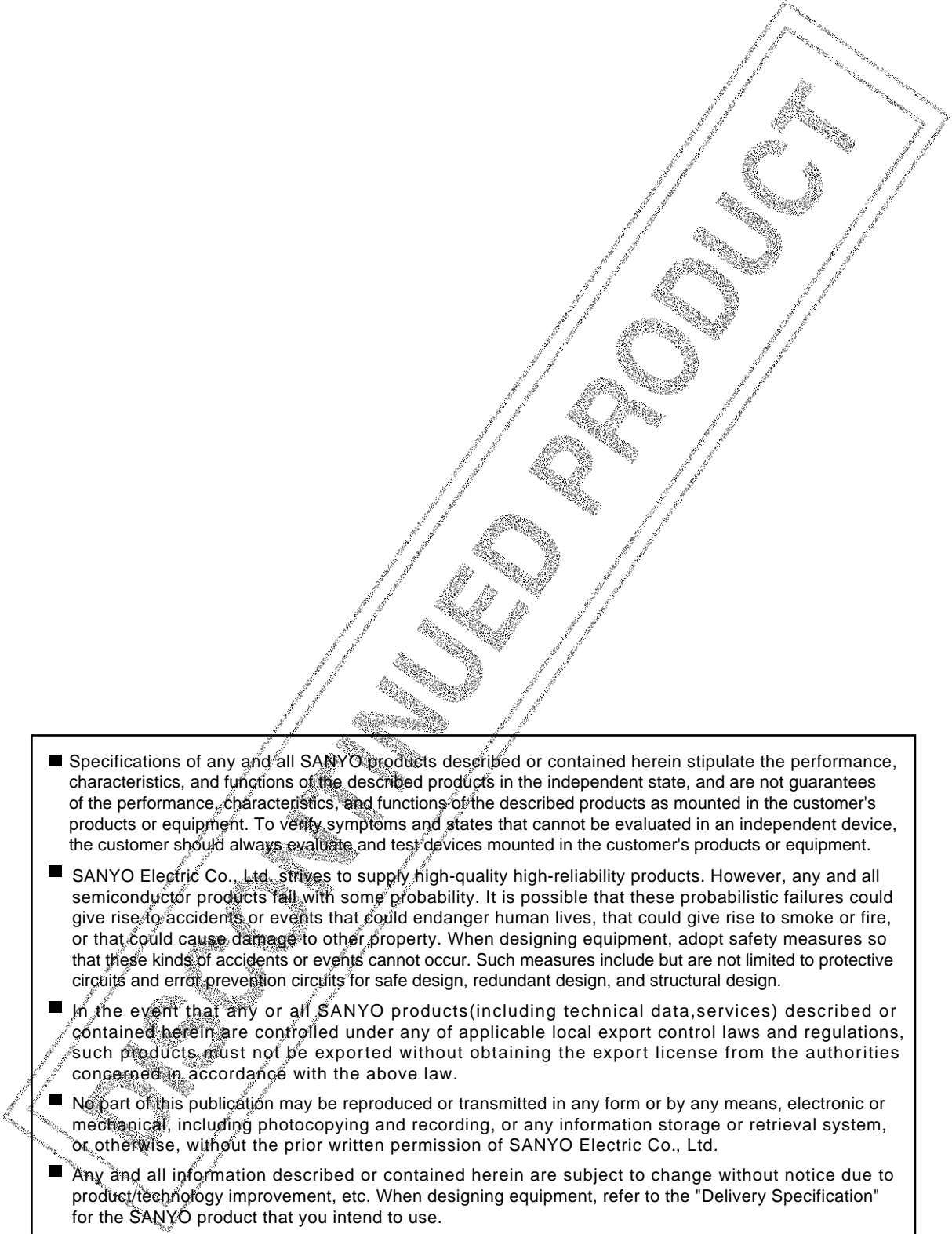
(Common gate) ($V_{DG}=5V$, $I_D=10mA$)



S parameter (Common gate)

$V_{DG}=5V$, $I_D=10mA$, $Z_0=50\Omega$

Freq (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
100	0.024	54.7	0.985	-9.7	0.059	21.9	0.942	-9.0
200	0.038	48.5	0.963	-18.8	0.078	30.1	0.918	-17.3
300	0.054	32.4	0.932	-27.3	0.097	30.2	0.896	-25.4
400	0.055	20.5	0.903	-35.4	0.113	27.3	0.870	-33.0
500	0.060	1.8	0.875	-43.6	0.124	23.4	0.847	-40.5
600	0.055	-19.1	0.849	-51.4	0.132	19.0	0.826	-48.2
700	0.053	-41.6	0.826	-60.1	0.137	15.0	0.811	-56.0

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